freescale
飞思卡尔(深圳)功率半导体有限公司

AO7402
N-Channel Enhancement Mode Field Effect Transistor

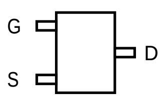
General Description

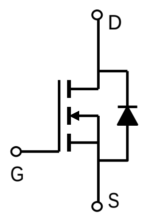
The AO7402 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V, in the small SOT323 footprint. It canbe used for a wide variety of applications, including load switching, low current inverters and low current DC-DC converters. *Standard Product AO7402 is Pb-free (meets ROHS & Sony 259 specifications). AO7402L is a Green Product ordering option. AO7402 and AO7402L are electrically identical.*

Features

V_{DS} (V) = 20V
I_D = 1.6 A (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 90mΩ (V_{GS} = 4.5V)
$R_{DS(ON)}$ < 105mΩ (V_{GS} = 2.5V)
$R_{DS(ON)}$ < 130mΩ (V_{GS} = 1.8V)

SC-70
(SOT-323)
Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted				
Parameter		**Symbol**	**Maximum**	**Units**
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [A]	T_A=25°C	I_D	1.6	A
	T_A=70°C		1.2	
Pulsed Drain Current [B]		I_{DM}	10	
Power Dissipation [A]	T_A=25°C	P_D	0.35	W
	T_A=70°C		0.22	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics					
Parameter		**Symbol**	**Typ**	**Max**	**Units**
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	300	360	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		340	425	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	280	320	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V		20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=16V, V_{GS}=0V				1	µA
			T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V				100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA		0.4	0.55	0.8	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V		10			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=1.6A			75	90	mΩ
			T_J=125°C		106	130	
		V_{GS}=2.5V, I_D=1.5A			86	105	mΩ
		V_{GS}=1.8V, I_D=1.4A			103	130	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=1.6A			5.5		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.69	1	V
I_S	Maximum Body-Diode Continuous Current					0.5	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=10V, f=1MHz			458		pF
C_{oss}	Output Capacitance				76		pF
C_{rss}	Reverse Transfer Capacitance				54		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz			3		Ω
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=10V, I_D=1.6A			6.05		nC
Q_{gs}	Gate Source Charge				0.7		nC
Q_{gd}	Gate Drain Charge				1.45		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=5V, V_{DS}=10V, R_L=6.25Ω, R_{GEN}=6Ω			7.3		ns
t_r	Turn-On Rise Time				5.6		ns
$t_{D(off)}$	Turn-Off DelayTime				40		ns
t_f	Turn-Off Fall Time				11		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=1.6A, dI/dt=100A/µs			12.2		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=1.6A, dI/dt=100A/µs			3.23		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80µs pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

Rev 3: Sept 2005

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

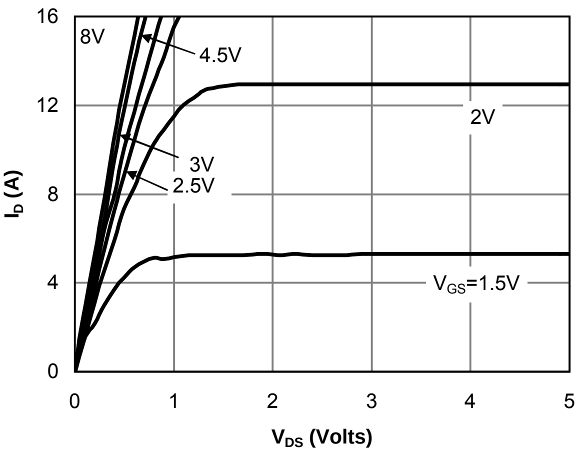


Fig 1: On-Region Characteristics

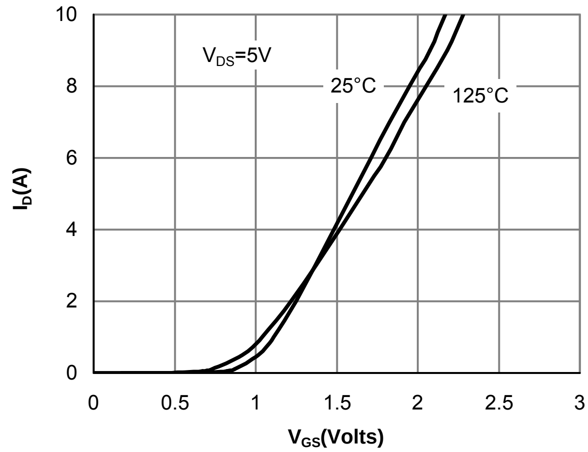


Figure 2: Transfer Characteristics

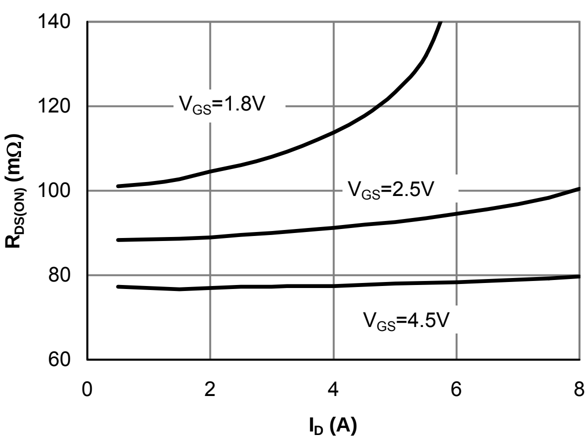


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

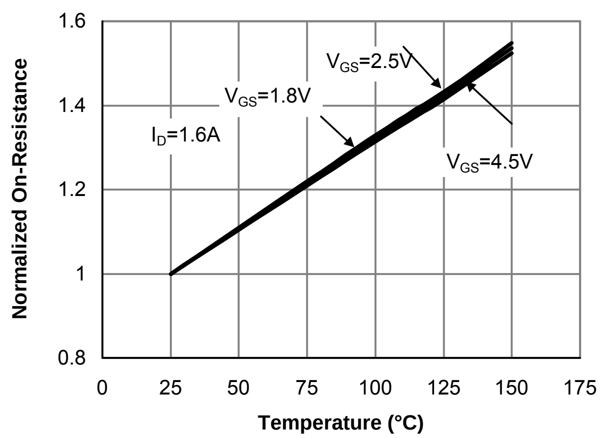


Figure 4: On-Resistance vs. Junction Temperature

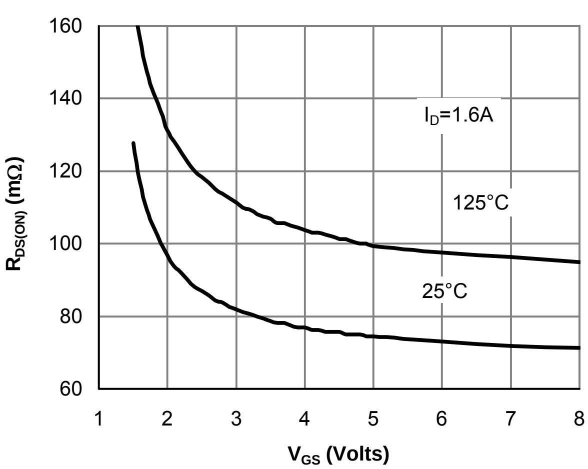


Figure 5: On-Resistance vs. Gate-Source Voltage

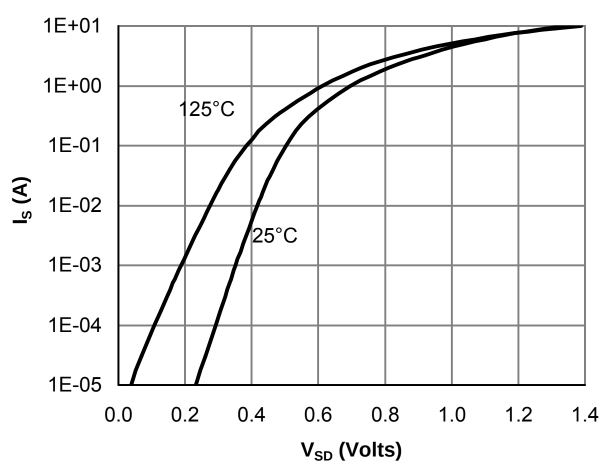


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

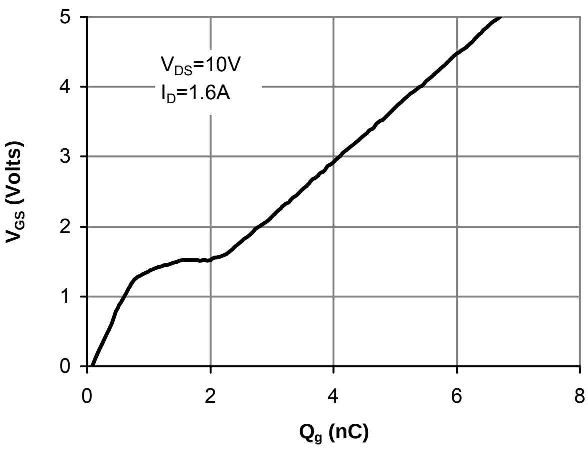


Figure 7: Gate-Charge Characteristics

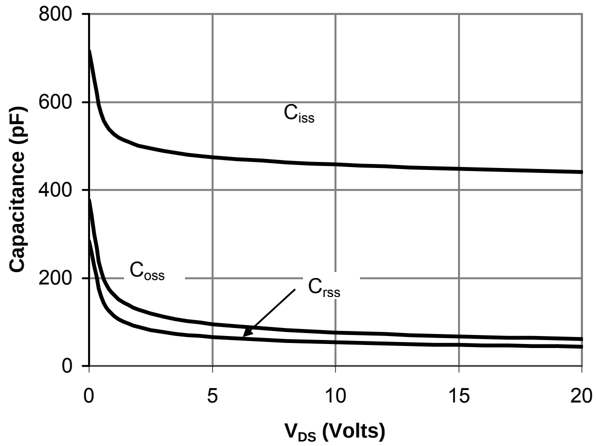


Figure 8: Capacitance Characteristics

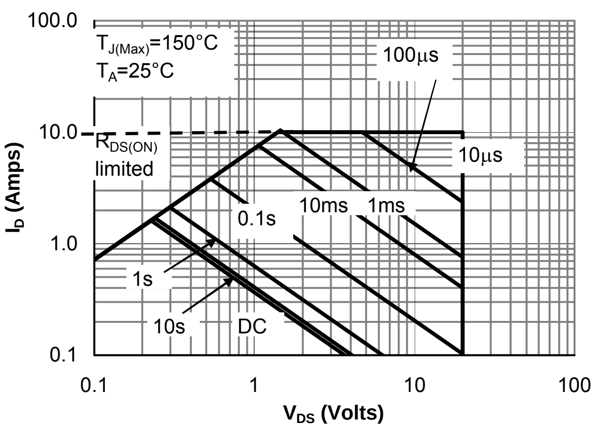


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

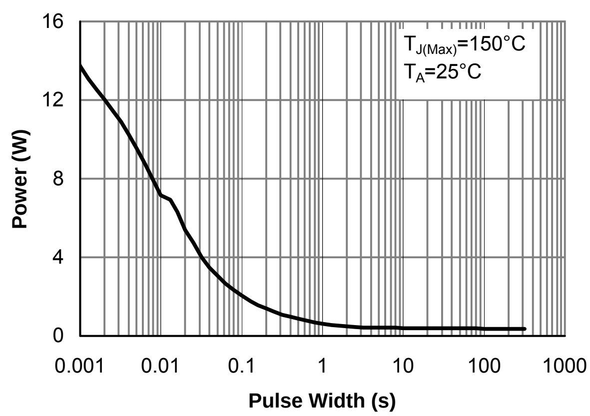


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

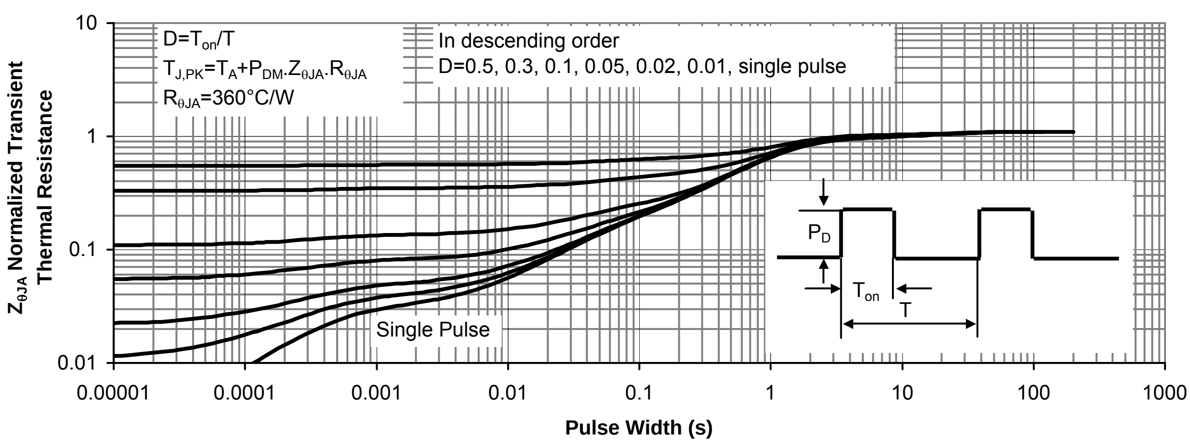


Figure 11: Normalized Maximum Transient Thermal Impedance